

To all our customers

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Renesas Technology Home Page: <http://www.renesas.com>

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SC4264

Silicon NPN Epitaxial

RENESAS

ADE-208-1101A (Z)

2nd. Edition

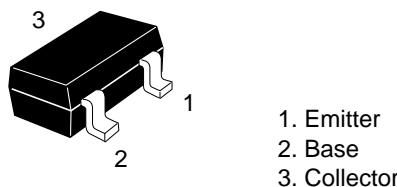
Mar. 2001

Application

VHF / UHF RF amplifier, Local oscillator, Mixer

Outline

CMPAK



1. Emitter
2. Base
3. Collector

Note: Marking is "GC".

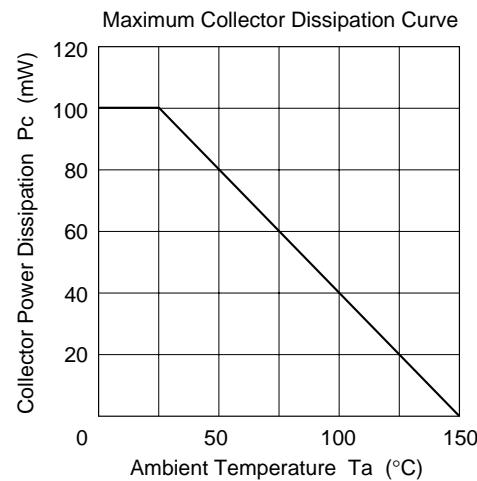
Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	20	V
Collector to emitter voltage	V _{CEO}	11	V
Emitter to base voltage	V _{EBO}	3	V
Collector current	I _C	50	mA
Collector power dissipation	P _C	100	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	−55 to +150	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	V _{(BR)CBO}	20	—	—	V	I _C = 10 µA, I _E = 0
Collector cutoff current	I _{CBO}	—	—	0.5	µA	V _{CB} = 15 V, I _E = 0
	I _{CEO}	—	—	10	µA	V _{CE} = 11 V, R _{BE} =
Emitter cutoff current	I _{EBO}	—	—	1.0	µA	V _{EB} = 3 V, I _C = 0
Collector to emitter saturation voltage	V _{CE(sat)}	—	—	0.7	V	I _C = 10 mA, I _B = 5 mA
DC current transfer ratio	h _{FE}	20	—	—		V _{CE} = 10 V, I _C = 5 mA
Collector output capacitance	C _{ob}	—	—	1.5	pF	V _{CB} = 10 V, I _E = 0, f = 1MHz
Gain bandwidth product	f _T	1.4	—	—	GHz	V _{CE} = 10 V, I _C = 10 mA

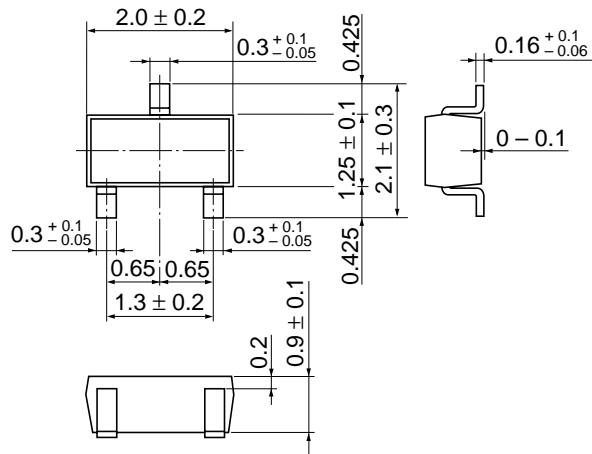
See characteristic curves of 2SC2734.



Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	CMPAK
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.006 g

Cautions

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	:	http://semiconductor.hitachi.com/
	Europe	:	http://www.hitachi-eu.com/hel/ecg
	Asia	:	http://sicapac.hitachi-asia.com
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For further information write to:

Hitachi Semiconductor (America) Inc.	Hitachi Europe GmbH
179 East Tasman Drive, San Jose, CA 95134	Electronic Components Group
Tel: <1> (408) 433-1990	Dornacher Straße 3
Fax: <1>(408) 433-0223	D-85622 Feldkirchen, Munich
	Tel: <49> (89) 9 9180-0
	Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel : <65>-538-6533/538-8577
Fax : <65>-538-6933/538-3877
URL : http://www.hitachi.com.sg

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel : <886>-(2)-2718-3666
Fax : <886>-(2)-2718-8180
Telex : 23222 HAS-TP
URL : http://www.hitachi.com.tw

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel : <852>-(2)-735-9218
Fax : <852>-(2)-730-0281
URL : http://www.hitachi.com.hk

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